

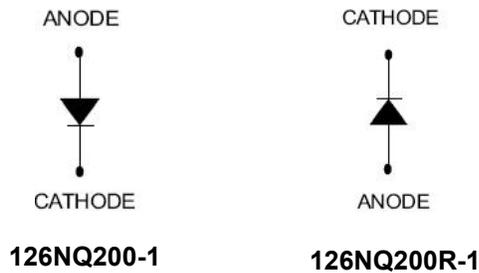
## 126NQ200/R-1 SCHOTTKY RECTIFIER



### Features

- 175°C T<sub>J</sub> operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5'S
- Easier to mount and lower profile than DO-5'S
- High purity, high temperature epoxy encapsulation for enhanced
- mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Base plate: Nickel plated; Terminals: Nickel plated
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

The top side is terminal, the bottom side is base plate.

### Maximum Ratings(limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	200	V
Average Forward Current	I <sub>F(AV)</sub>	50% duty cycle @T <sub>C</sub> =110°C, rectangular wave form	120	A
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	2500	A

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 120A, Pulse, T <sub>J</sub> = 25 °C	0.88	1.12	V
	V <sub>F2</sub>	@ 120A, Pulse, T <sub>J</sub> = 125 °C	0.77	0.79	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	0.2	3000	uA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	0.2	45	mA
Junction Capacitance	C <sub>T</sub>	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	1500	1800	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

\* Pulse width < 300 μs, duty cycle < 2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification		Units
Junction Temperature	T <sub>J</sub>	-	-55 to +175		°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case	R <sub>θJC</sub>	DC operation	0.25		°C/W
Typical Thermal Resistance, case to Heat Sink	R <sub>θcs</sub>	Mounting surface, smooth and greased	0.07		°C/W
Mounting Torque	T <sub>M</sub>	Non-lubricated threads	Mounting Torque	23(min) 29(max)	Kg-cm
			Terminal Torque	35(min) 46(max)	
Approximate Weight	wt	-	36		g
Case Style	PRM1-1				

**Ratings and Characteristics Curves**

Figure 1  
Typical Forward Characteristics

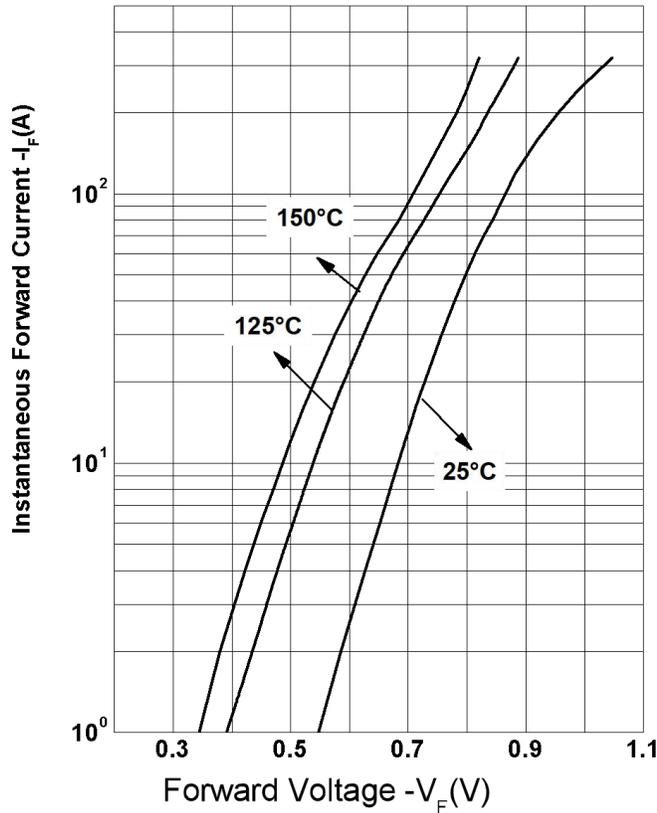


Figure 2  
Typical Reverse Characteristics

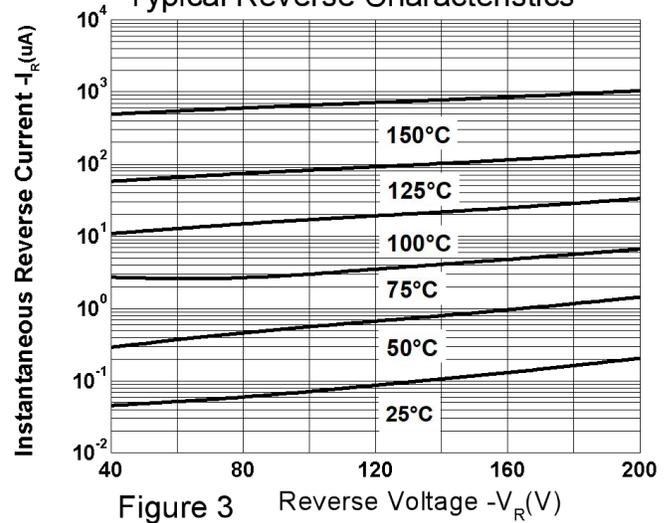
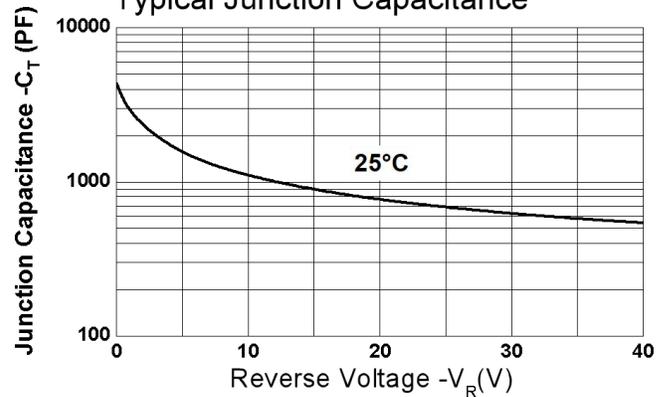


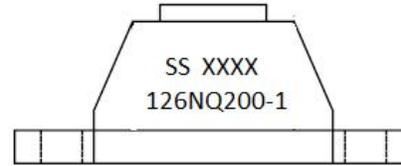
Figure 3  
Typical Junction Capacitance



**Ordering Information**

Device	Package	Shipping
126NQ200(R)-1	PRM1-1(Pb-Free)	27pcs/ box

**Marking Diagram**

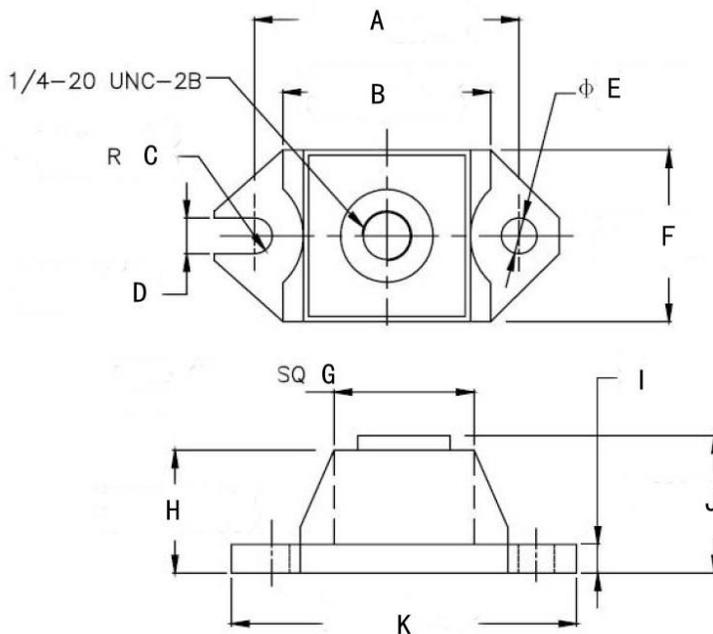


Where XXXX is YYWW

1st row SS YYWW  
2nd row 126NQ200-1  
SS = SS  
YY = Year  
WW = Week

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Mechanical Dimensions PRM1-1 (Inches/Millimeters)**



SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	29.35	30.95	1.155	1.219
B	24.77	26.04	0.975	1.026
C	1.79	2.19	0.070	0.087
D	3.73	4.24	0.146	0.167
E	3.73	4.24	0.146	0.167
F	18.42	19.69	0.725	0.775
G	18.55	19.55	0.730	0.770
H	13.59	14.47	0.535	0.570
I	3.05	3.90	0.120	0.154
J	14.87	15.87	0.585	0.625
K	38.61	39.62	1.520	1.560

**Technical Data**  
**Data Sheet N1166, Rev. A**



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